

[STRUCTURE OF QUANTUM DOT LIGHT EMITTING DIODE AND METHOD OF FAB- RICATING THE SAME]

Abstract

An InAs/GaAs quantum dot light emitting diode and a method of fabricating the same are disclosed. The InAs/GaAs quantum dot light emitting diode which is formed by turning off an As shutter and using As background concentration for epitaxy, comprises a Si-doped GaAs substrate, a N-type structure, an undoped quantum well, a series of quantum dot layers, spacer layers, a barrier layer and a P-type structure.